

PNP/NPN Epitaxial Planar Silicon Transistors

2SA1419/2SC3649



High-Voltage Switching Applications

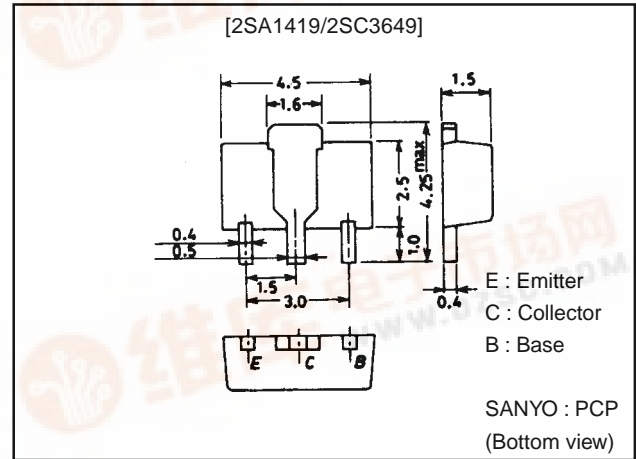
Features

- Adoption of FBET, MBIT processes.
- High breakdown voltage and large current capacity.
- Very small size making it easy to provide high-density hybrid ICs.

Package Dimensions

unit:mm

2038



() : 2SA1419

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB0}		(-)180	V
Collector-to-Emitter Voltage	V_{CEO}		(-)160	V
Emitter-to-Base Voltage	V_{EBO}		(-)6	V
Collector Current	I_C		(-)1.5	A
Collector Current (Pulse)	I_{CP}		(-)2.5	A
Collector Dissipation	P_C		500	mW
		Mounted on ceramic board (250mm ² ×0.8mm)	1.5	W
Junction Temperature	T_J		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)120V, I_E = 0$			(-)1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)1	μA
DC Current Gain	h_{FE1}	$V_{CE} = (-)5V, I_C = (-)100mA$	100*		400*	
	h_{FE2}	$V_{CE} = (-)5V, I_C = (-)10mA$	80			
Gain-Bandwidth Product	f_T	$V_{CE} = (-)10V, I_C = (-)50mA$		120		MHz
Output Capacitance	C_{ob}	$V_{CB} = (-)10V, f = 1MHz$		(22)		pF
				14		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)500mA, I_B = (-)50mA$		(-200)	(-500)	mV
				130	450	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)500mA, I_B = (-)50mA$		(-)0.85	(-)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10μA, I_E = 0$	(-)180			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = ∞$	(-)160			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10μA, I_C = 0$	(-)6			V
Turn-ON Time	t_{on}	See specified Test Circuit.		(40)		ns
				40		ns
Storage Time	t_{stg}	See specified Test Circuit.		(0.7)		μs
				1.2		μs
Fall Time	t_f	See specified Test Circuit.		(40)		ns
				80		ns



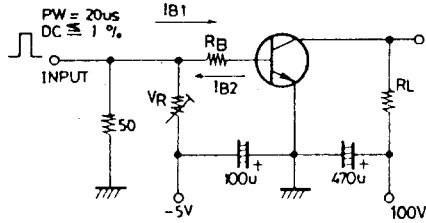
2SA1419/2SC3649

* : The 2SA1419/2SC3649 are classified by 100mA h_{FE} as follows :

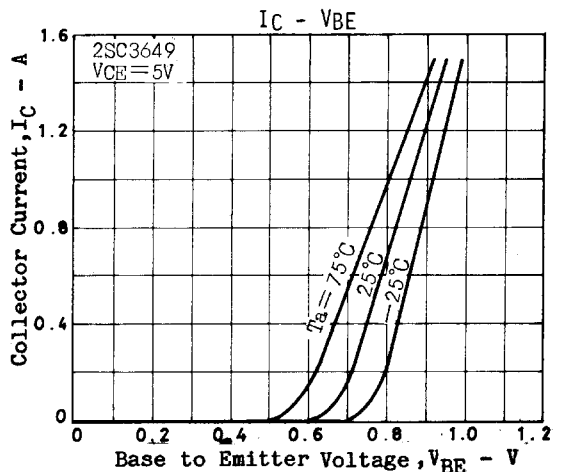
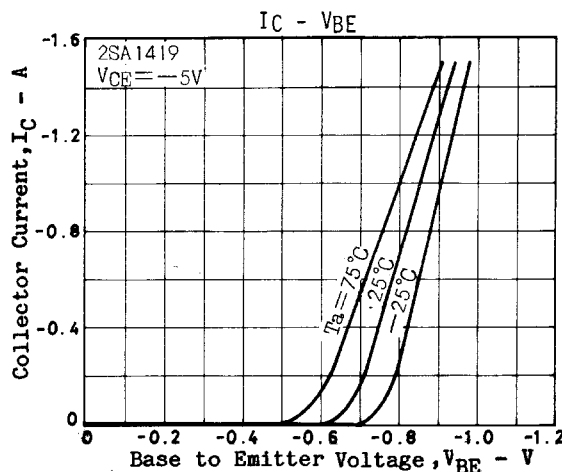
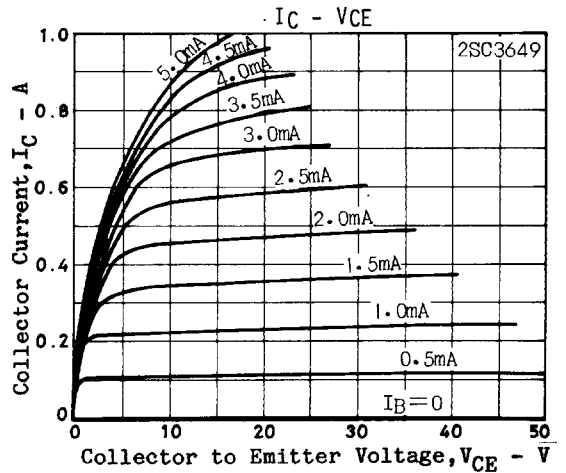
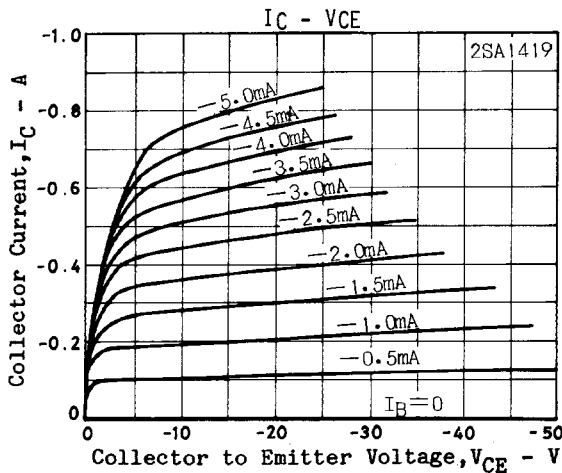
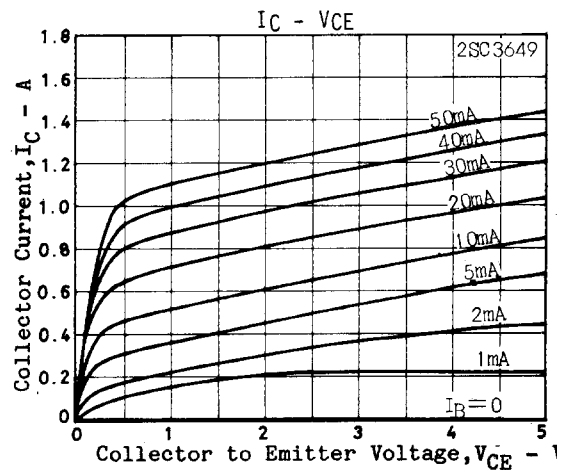
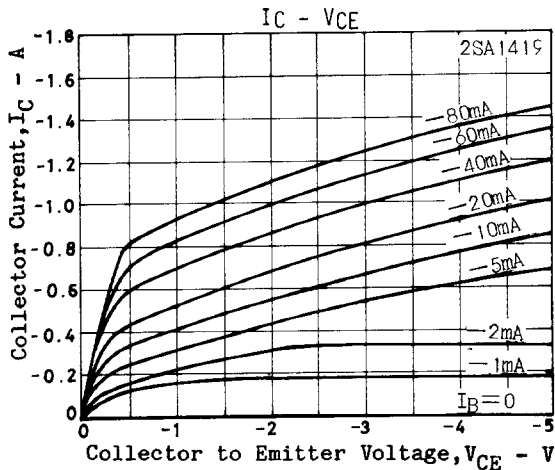
100	R	200	140	S	280	200	T	400
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Marking 2SA1419 : AE h_{FE} rank : R, S, T
 2SC3649 : CE

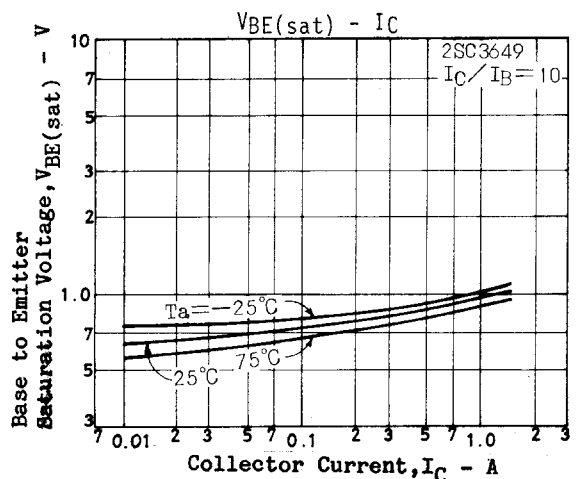
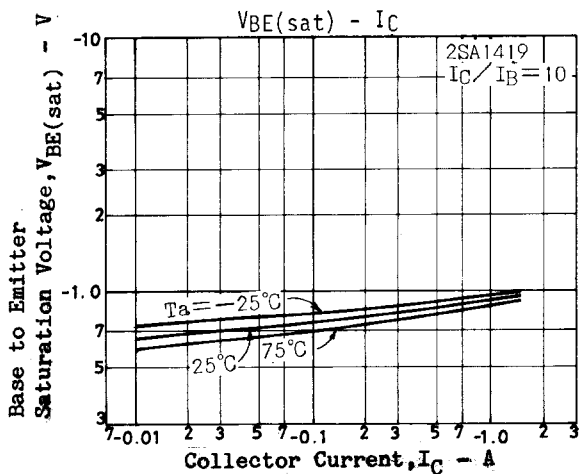
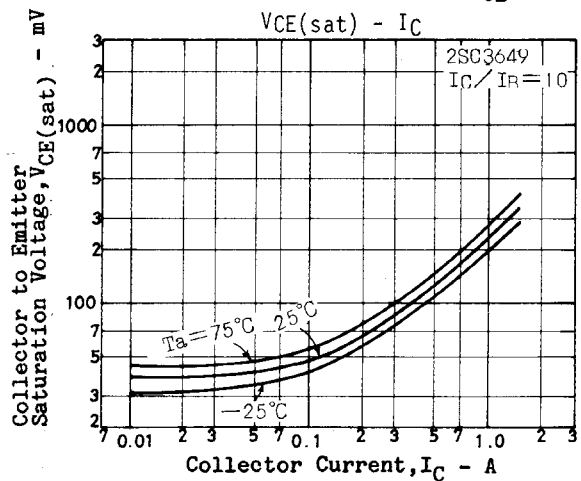
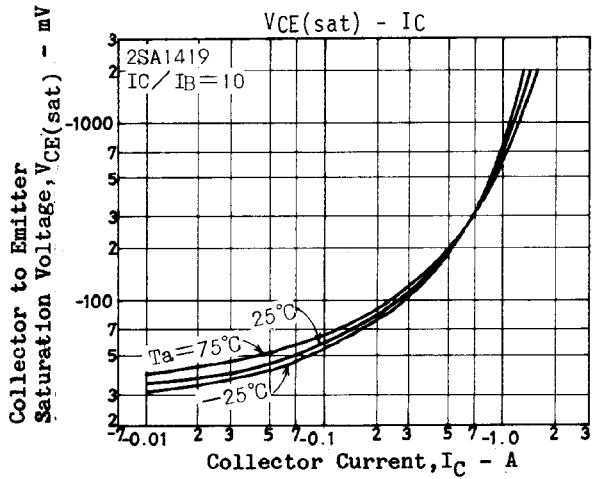
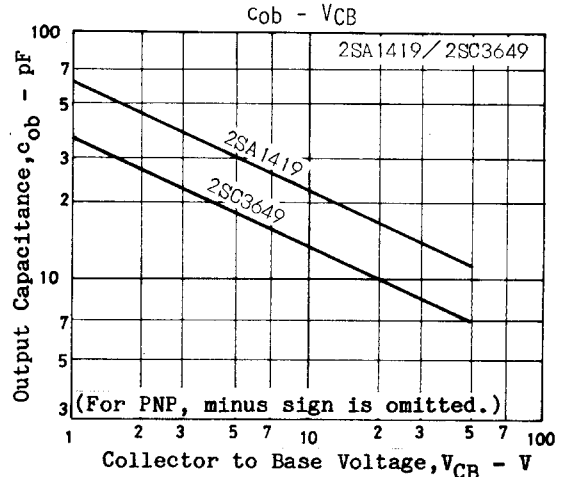
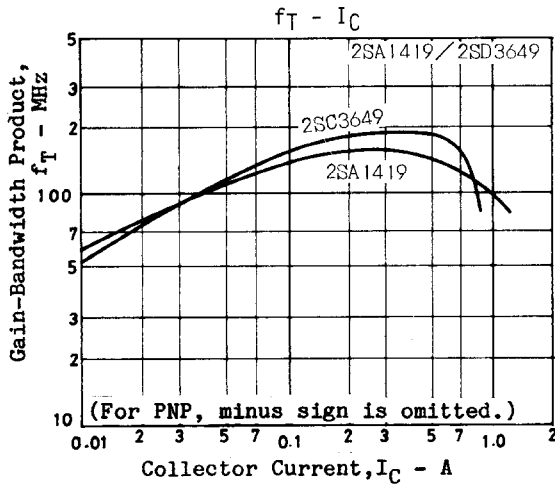
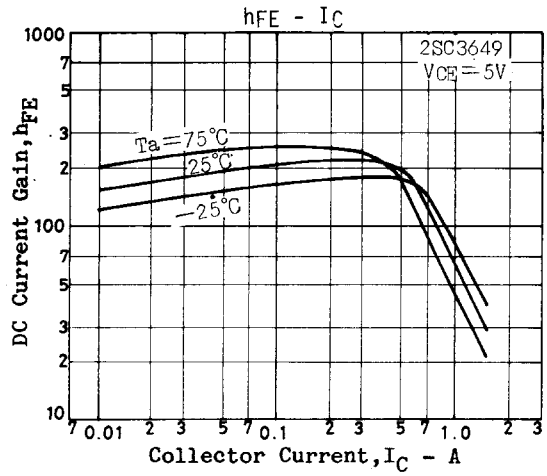
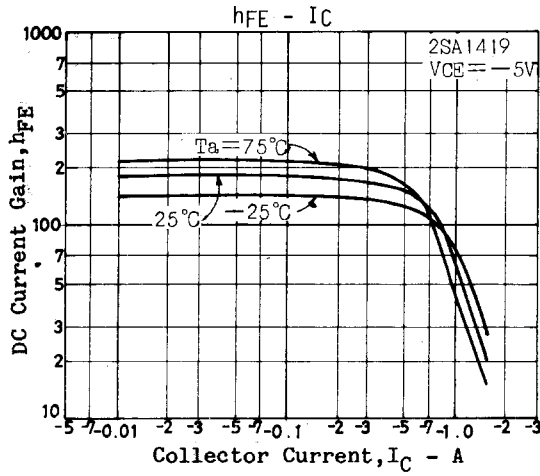
Switching Time Test Circuit



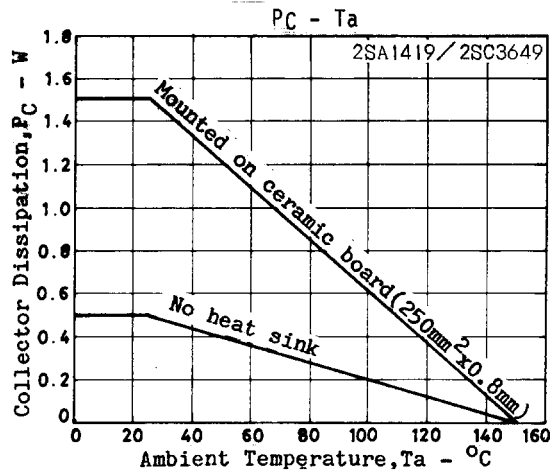
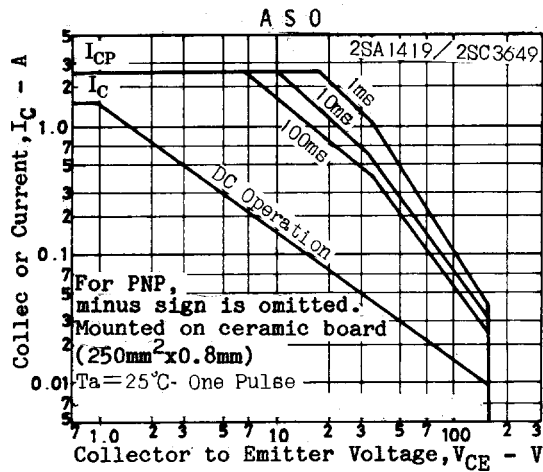
(For PNP, the polarity is reversed)
 Unit (resistance : Ω , capacitance : F)



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